

7-46-23-10 **CY7C164A**  
**CY7C166A**



CYPRESS  
SEMICONDUCTOR

16,384 x 4 Static R/W RAM

**Features**

- Automatic power-down when deselected
- Output Enable ( $\overline{OE}$ ) feature (7C166A)
- CMOS for optimum speed/power
- High speed
  - $t_{AA} = 15$  ns
- Low active power
  - 550 mW
- Low standby power
  - 220 mW
- TTL-compatible inputs and outputs
- Capable of withstanding greater than 2001V electrostatic discharge

**Functional Description**

The CY7C164A and CY7C166A are high-performance CMOS static RAMs organized as 16,384 by 4 bits. Easy memory expansion is provided by an active LOW chip enable ( $\overline{CE}$ ) and three-state drivers. The CY7C166A has an active low output enable ( $\overline{OE}$ ) feature. Both devices have an automatic power-down feature, reducing the power consumption by 60% when deselected.

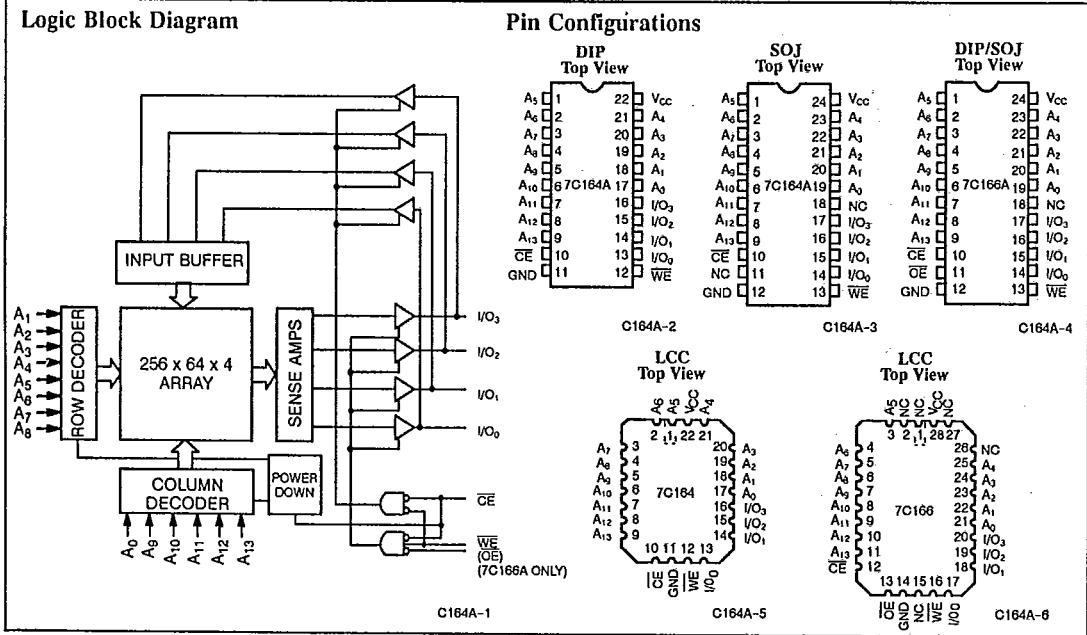
Writing to the device is accomplished when the chip enable ( $\overline{CE}$ ) and write enable ( $\overline{WE}$ ) inputs are both LOW (and the output enable ( $\overline{OE}$ ) is LOW for the 7C166A). Data on the four input/output pins ( $I/O_0$  through

$I/O_3$ ) is written into the memory location specified on the address pins ( $A_0$  through  $A_{13}$ ).

Reading the device is accomplished by taking chip enable ( $\overline{CE}$ ) LOW (and  $\overline{OE}$  LOW for 7C166A), while write enable ( $\overline{WE}$ ) remains HIGH. Under these conditions the contents of the memory location specified on the address pins will appear on the four data I/O pins.

The I/O pins stay in high-impedance state when chip enable ( $\overline{CE}$ ) is HIGH, or write enable ( $\overline{OE}$ ) is HIGH for 7C166A).

A die coat is used to insure alpha immunity.



**Selection Guide**

		7C164A-15 7C166A-15	7C164A-20 7C166A-20	7C164A-25 7C166A-25	7C164A-35 7C166A-35	7C164A-45 7C166A-45
Maximum Access Time (ns)		15	20	25	35	45
Maximum Operating Current (mA)	Commercial	115	100	100	100	100
	Military		100	100	100	100
Maximum Standby Current (mA)	Commercial	40/20	40/20	30	30	30
	Military		40/20	40/20	30	30



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**Maximum Ratings**

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... - 65°C to + 150°C  
 Ambient Temperature with  
 Power Applied ..... - 55°C to + 125°C  
 Supply Voltage to Ground Potential ..... - 0.5V to + 7.0V  
 DC Voltage Applied to Outputs  
 in High Z State ..... - 0.5V to + 7.0V  
 DC Input Voltage ..... - 3.0V to + 7.0V  
 Output Current into Outputs (Low) ..... 20 mA

Static Discharge Voltage ..... >2001V  
 (per MIL-STD-883, Method 3015)  
 Latch-up Current ..... >200 mA

**Operating Range**

Range	Ambient Temperature	V <sub>CC</sub>
Commercial	0°C to + 70°C	5V ± 10%
Military <sup>[1]</sup>	- 55°C to + 125°C	5V ± 10%



**Electrical Characteristics Over the Operating Range<sup>[2]</sup>**

Parameters	Description	Test Conditions	7C164A-15 7C166A-15		7C164A-20 7C166A-20		Units
			Min.	Max.	Min.	Max.	
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min., I <sub>OH</sub> = - 4.0 mA	2.4		2.4		V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min., I <sub>OL</sub> = 8.0 mA		0.4		0.4	V
V <sub>IH</sub>	Input HIGH Voltage		2.2	V <sub>CC</sub>	2.2	V <sub>CC</sub>	V
V <sub>IL</sub>	Input LOW Voltage <sup>[3]</sup>		-3.0	0.8	-3.0	0.8	V
I <sub>IX</sub>	Input Load Current	GND ≤ V <sub>I</sub> ≤ V <sub>CC</sub>	-10	+ 10	-10	+ 10	μA
I <sub>OZ</sub>	Output Leakage Current	GND ≤ V <sub>O</sub> ≤ V <sub>CC</sub> , Output Disabled	-10	+ 10	-10	+ 10	μA
I <sub>OS</sub>	Output Short Circuit Current <sup>[4]</sup>	V <sub>CC</sub> = Max., V <sub>OUT</sub> = GND		-350		-350	mA
I <sub>CC</sub>	V <sub>CC</sub> Operating Supply Current	V <sub>CC</sub> = Max. I <sub>OUT</sub> = 0 mA	Com'l	115		100	mA
			Mil			100	
I <sub>SB1</sub>	Automatic $\overline{CE}$ <sup>[5]</sup> Power Down Current	Max. V <sub>CC</sub> , $\overline{CE} \geq V_{IH}$ Min. Duty Cycle = 100%	Com'l	40		40	mA
			Mil			40	
I <sub>SB2</sub>	Automatic $\overline{CE}$ <sup>[5]</sup> Power Down Current	Max. V <sub>CC</sub> , $\overline{CE} \geq V_{IH} - 0.3V$ $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$	Com'l	20		20	mA
			Mil			20	

**Notes:**

1. T<sub>A</sub> is the "instant on" case temperature.
2. See the last page of this specification for Group A subgroup testing information.
3. V<sub>IL</sub> min. = - 3.0V for pulse durations less than 30 ns.
4. Not more than 1 output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
5. A pull-up resistor to V<sub>CC</sub> on the  $\overline{CE}$  input is required to keep the device deselected during V<sub>CC</sub> power-up, otherwise I<sub>SB</sub> will exceed values given.
6. Tested initially and after any design or process changes that may affect these parameters.



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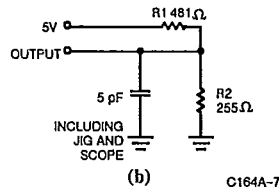
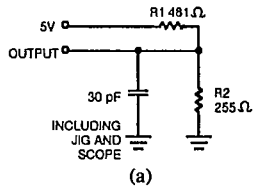
Electrical Characteristics Over the Operating Range <sup>[2]</sup>(continued)

Parameters	Description	Test Conditions	7C164A-25 7C166A-25		7C164A-35,45 7C166A-35,45		Units
			Min.	Max.	Min.	Max.	
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = Min., I <sub>OH</sub> = -4.0 mA	2.4		2.4		V
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = Min., I <sub>OL</sub> = 8.0 mA		0.4		0.4	V
V <sub>IH</sub>	Input HIGH Voltage		2.2	V <sub>CC</sub>	2.2	V <sub>CC</sub>	V
V <sub>IL</sub>	Input LOW Voltage <sup>[3]</sup>		-3.0	0.8	-3.0	0.8	V
I <sub>IX</sub>	Input Load Current	GND ≤ V <sub>I</sub> ≤ V <sub>CC</sub>	-10	+10	-10	+10	μA
I <sub>oz</sub>	Output Leakage Current	GND ≤ V <sub>O</sub> ≤ V <sub>CC</sub> , Output Disabled	-10	+10	-10	+10	μA
I <sub>os</sub>	Output Short Circuit Current <sup>[4]</sup>	V <sub>CC</sub> = Max., V <sub>OUT</sub> = GND		-350		-350	mA
I <sub>CC</sub>	V <sub>CC</sub> Operating Supply Current	V <sub>CC</sub> = Max. I <sub>OUT</sub> = 0 mA	Com'l	100		100	mA
			Mil		100		
I <sub>SB1</sub>	Automatic $\overline{CE}$ <sup>[5]</sup> Power Down Current	Max. V <sub>CC</sub> , $\overline{CE} \geq V_{IH}$ Min. Duty Cycle = 100%	Com'l	30		30	mA
			Mil		40		
I <sub>SB2</sub>	Automatic $\overline{CE}$ <sup>[5]</sup> Power Down Current	Max. V <sub>CC</sub> , $\overline{CE} \geq V_{IH} - 0.3V$ V <sub>IN</sub> ≥ V <sub>CC</sub> - 0.3V or V <sub>IN</sub> ≤ 0.3V	Com'l	20		20	mA
			Mil		20		

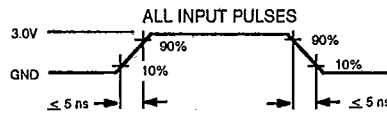
Capacitance<sup>[6]</sup>

Parameters	Description	Test Conditions	Max.	Units
C <sub>IN</sub>	Input Capacitance	T <sub>A</sub> = 25°C, f = 1 MHz, V <sub>CC</sub> = 5.0V	10	pF
C <sub>OUT</sub>	Output Capacitance		10	pF

AC Test Loads and Waveforms



C164A-7



C164A-8

Equivalent to: THEVENIN EQUIVALENT  
167Ω  
OUTPUT ○ ———— 1.73V



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Switching Characteristics Over the Operating Range<sup>(2,7)</sup>

Parameters	Description	7C164A-15 7C166A-15		7C164A-20 7C166A-20		7C164A-25 7C166A-25		7C164A-35 7C166A-35		7C164A-45 7C166A-45		Units
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
<b>READ CYCLE</b>												
t <sub>RC</sub>	Read Cycle Time	15		20		25		35		45		ns
t <sub>AA</sub>	Address to Data Valid		15		20		25		35		45	ns
t <sub>OHA</sub>	Output Hold from Address Change	3		3		3		3		3		ns
t <sub>ACE</sub>	$\overline{CE}$ LOW to Data Valid		15		20		25		35		45	ns
t <sub>DOB</sub>	$\overline{OE}$ LOW to Data Valid		10		10		12		15		20	ns
t <sub>LHZOE</sub>	$\overline{OE}$ LOW to LOW Z	3		3		3		3		3		ns
t <sub>LZOE</sub>	$\overline{OE}$ HIGH to HIGH Z		8		8		10		12		15	ns
t <sub>LZCE</sub>	$\overline{CE}$ LOW to Low Z <sup>(8)</sup>	3		5		5		5		5		ns
t <sub>HZCE</sub>	$\overline{CE}$ HIGH to High Z <sup>(8,9)</sup>		8		8		10		15		15	ns
t <sub>PU</sub>	$\overline{CE}$ LOW to Power-Up	0		0		0		0		0		ns
t <sub>PD</sub>	$\overline{CE}$ HIGH to Power-Down		15		20		20		20		25	ns
<b>WRITE CYCLE<sup>(10)</sup></b>												
t <sub>WC</sub>	Write Cycle Time	15		20		20		25		40		ns
t <sub>SCE</sub>	$\overline{CE}$ LOW to Write End	12		15		20		25		30		ns
t <sub>AW</sub>	Address Set-Up to Write End	12		15		20		25		30		ns
t <sub>HA</sub>	Address Hold from Write End	0		0		0		0		0		ns
t <sub>SA</sub>	Address Set-Up to Write Start	0		0		0		0		0		ns
t <sub>PWE</sub>	$\overline{WE}$ Pulse Width	12		15		15		20		20		ns
t <sub>SD</sub>	Data Set-Up to Write End	10		10		10		15		15		ns
t <sub>HD</sub>	Data Hold from Write End	0		0		0		0		0		ns
t <sub>LZWE</sub>	$\overline{WE}$ HIGH to Low Z <sup>(8)</sup>	5		5		5		5		5		ns
t <sub>HZWE</sub>	$\overline{WE}$ LOW to High Z <sup>(8,9)</sup>		7		7		7		10		15	ns

Notes:

- Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I<sub>OL</sub>/I<sub>OH</sub> and 30-pF load capacitance.
- At any given temperature and voltage condition, t<sub>HZCE</sub> is less than t<sub>LZCE</sub> for any given device. These parameters are guaranteed and not 100% tested.
- t<sub>HZCE</sub> and t<sub>HZWE</sub> are specified with C<sub>L</sub> = 5 pF as in part (b) in AC Test Loads. Transition is measured ± 500 mV from steady state voltage.
- The internal write time of the memory is defined by the overlap of  $\overline{CE}$  LOW and  $\overline{WE}$  LOW. Both signals must be LOW to initiate a write and

either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

- $\overline{WE}$  is HIGH for read cycle.
- Device is continuously selected,  $\overline{CE} = V_{IL}$ . (7C166:  $\overline{OE} = V_{IL}$  also).
- Address valid prior to or coincident with  $\overline{CE}$  transition low.
- 7C166 only: Data I/O will be high impedance if  $\overline{OE} = V_{IH}$ .
- If  $\overline{CE}$  goes HIGH simultaneously with  $\overline{WE}$  HIGH, the output remains in a high-impedance state.

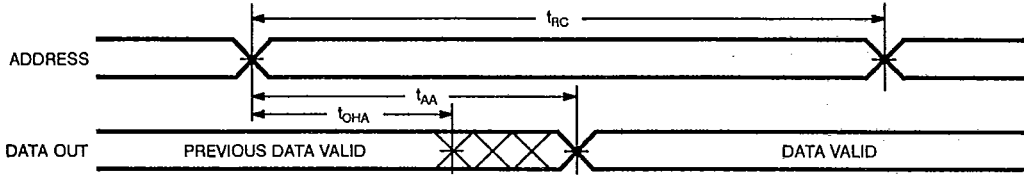


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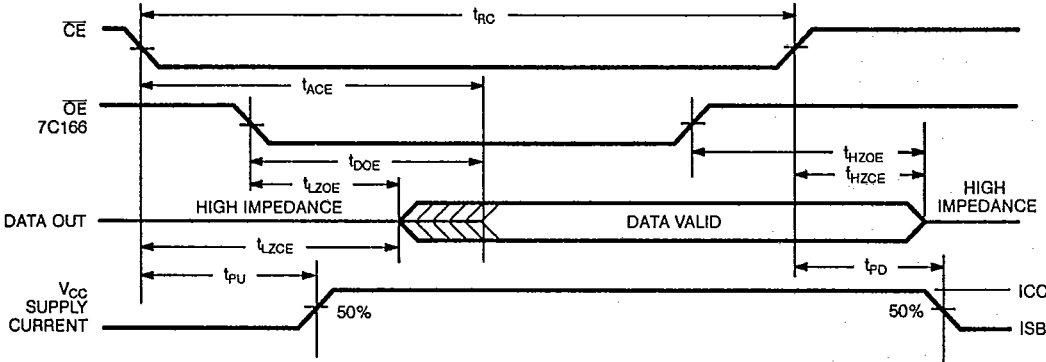
Switching Waveforms

Read Cycle No. 1<sup>[11, 12]</sup>



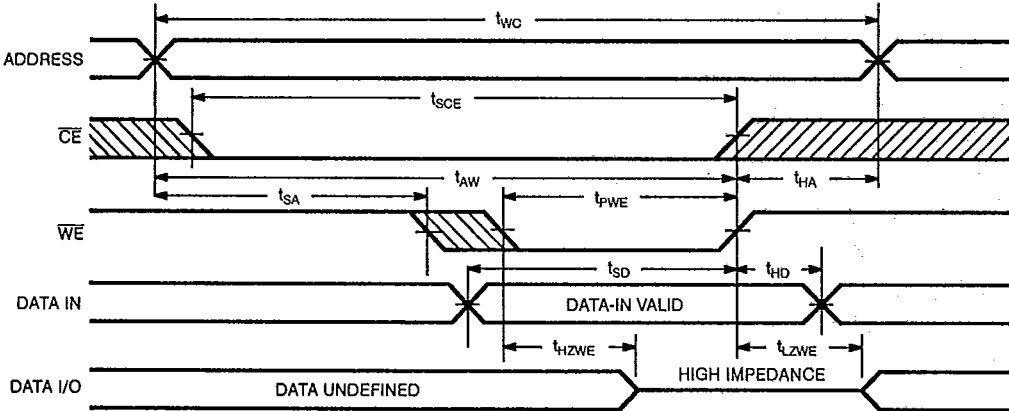
C164A-9

Read Cycle No. 2<sup>[11, 13]</sup>



C164A-10

Write Cycle No. 1 (WE Controlled)<sup>[10, 14]</sup>



C164A-11

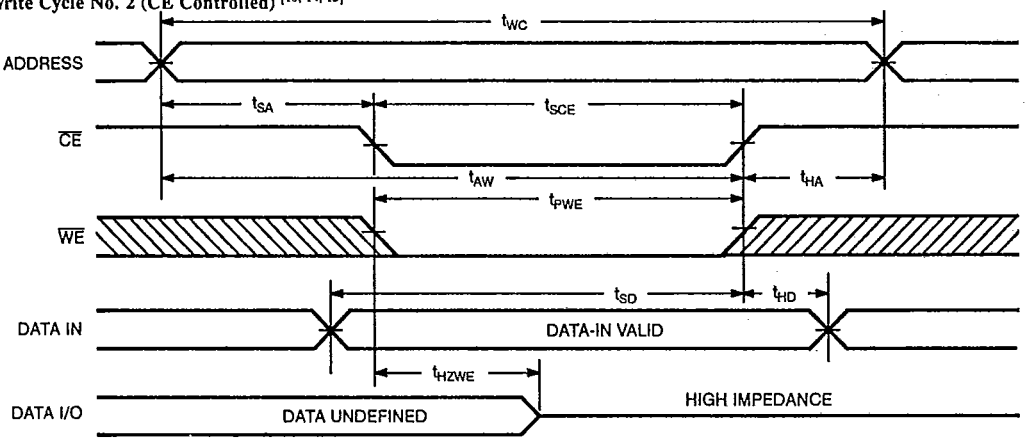


CY7C164A  
CY7C166A

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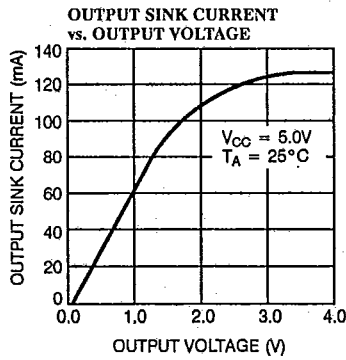
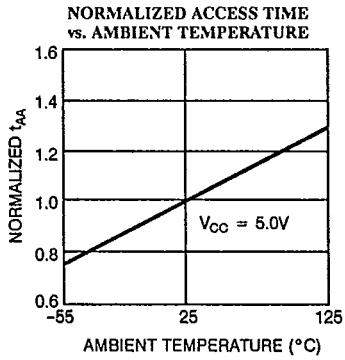
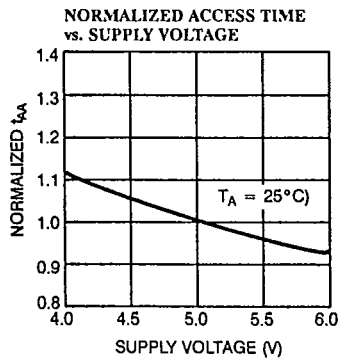
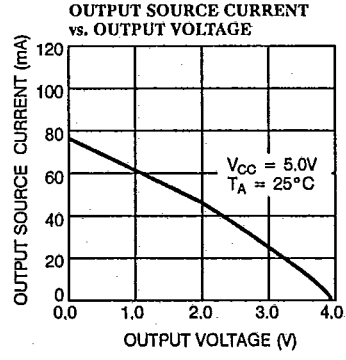
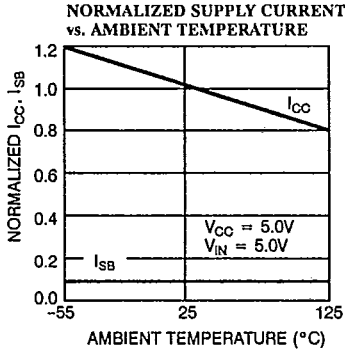
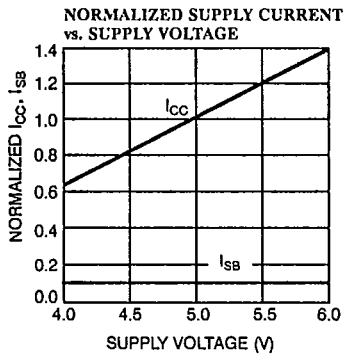
Switching Waveforms (continued)

Write Cycle No. 2 (CE Controlled) [10, 14, 15]



C164A-12

Typical DC and AC Characteristics

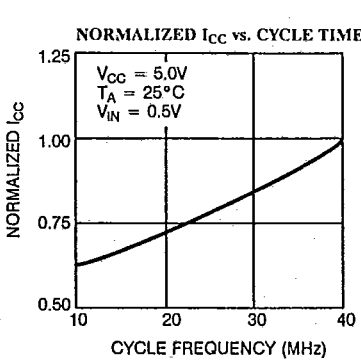
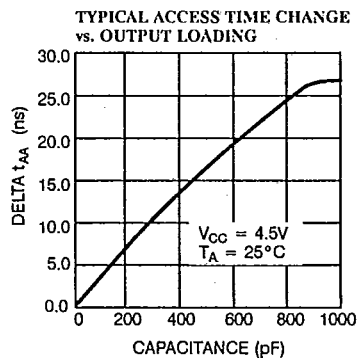
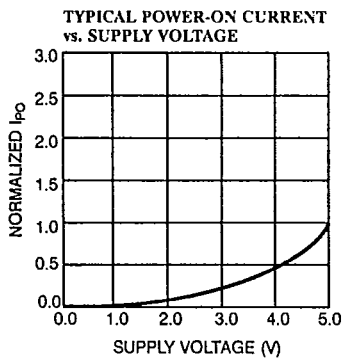




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Typical DC and AC Characteristics (continued)

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7C164A Truth Table

$\overline{CE}$	$\overline{WE}$	Inputs/Outputs	Mode
H	X	High Z	Deselect/Power-Down
L	H	Data Out	Read
L	L	Data In	Write

7C166A Truth Table

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	Inputs/Outputs	Mode
H	X	X	High Z	Deselect/Power-Down
L	H	L	Data Out	Read
L	L	X	Data In	Write
L	H	H	High Z	Deselect



CY7C164A  
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Ordering Information

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Speed (ns)	Ordering Code	Package Type	Operating Range
15	CY7C164A-15PC	P9	Commercial
	CY7C164A-15VC	V13	
	CY7C164A-15DC	D10	
	CY7C164A-15LC	L52	
20	CY7C164A-20PC	P9	Commercial
	CY7C164A-20VC	V13	
	CY7C164A-20DC	D10	
	CY7C164A-20LC	L52	
	CY7C164A-20DMB	D10	Military
	CY7C164A-20LMB	L52	
	CY7C164A-20KMB	K73	
25	CY7C164A-25PC	P9	Commercial
	CY7C164A-25VC	V13	
	CY7C164A-25DC	D10	
	CY7C164A-25LC	L52	
	CY7C164A-25DMB	D10	Military
	CY7C164A-25LMB	L52	
	CY7C164A-25KMB	K73	
35	CY7C164A-35PC	P9	Commercial
	CY7C164A-35VC	V13	
	CY7C164A-35DC	D10	
	CY7C164A-35LC	L52	
	CY7C164A-35DMB	D10	Military
	CY7C164A-35LMB	L52	
	CY7C164A-35KMB	K73	
45	CY7C164A-45PC	P9	Commercial
	CY7C164A-45VC	V13	
	CY7C164A-45DC	D10	
	CY7C164A-45LC	L52	
	CY7C164A-45DMB	D10	Military
	CY7C164A-45LMB	L52	
	CY7C164A-45KMB	K73	

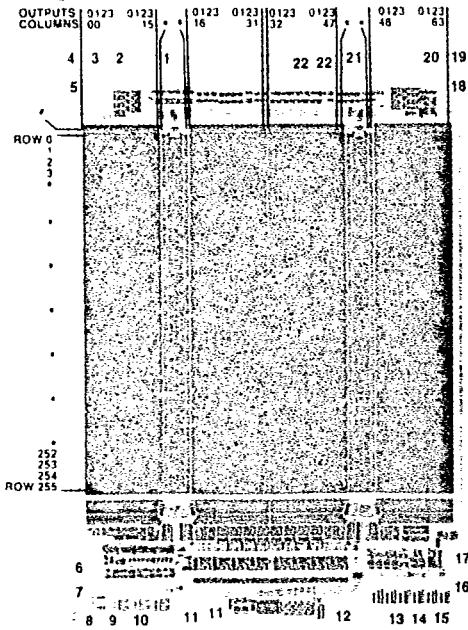
Speed (ns)	Ordering Code	Package Type	Operating Range
15	CY7C166A-15PC	P13	Commercial
	CY7C166A-15VC	V13	
	CY7C166A-15DC	D10	
	CY7C166A-15LC	L52	
20	CY7C166A-20PC	P13	Commercial
	CY7C166A-20VC	V13	
	CY7C166A-20DC	D14	
	CY7C166A-20LC	L54	
	CY7C166A-20DMB	D14	Military
	CY7C166A-20LMB	L54	
	CY7C166A-20KMB	K73	
25	CY7C166A-25PC	P13	Commercial
	CY7C166A-25VC	V13	
	CY7C166A-25DC	D14	
	CY7C166A-25LC	L54	
	CY7C166A-25DMB	D14	Military
	CY7C166A-25LMB	L54	
	CY7C166A-25KMB	K73	
35	CY7C166A-35PC	P13	Commercial
	CY7C166A-35VC	V13	
	CY7C166A-35DC	D14	
	CY7C166A-35LC	L54	
	CY7C166A-35DMB	D14	Military
	CY7C166A-35LMB	L54	
	CY7C166A-35KMB	K73	
45	CY7C166A-45PC	P13	Commercial
	CY7C166A-45VC	V13	
	CY7C166A-45DC	D14	
	CY7C166A-45LC	L54	
	CY7C166A-45DMB	D14	Military
	CY7C166A-45LMB	L54	
	CY7C166A-45KMB	K73	







Bit Map



Address Designators

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Address Name	Address Function	Pin Number
A5	X3	1
A6	X4	2
A7	X5	3
A8	X6	4
A9	X7	5
A10	Y5	6
A11	Y4	7
A12	Y0	8
A13	Y1	9
A0	Y2	17
A1	Y3	18
A2	X0	19
A3	X1	20
A4	X2	21

MILITARY SPECIFICATIONS

Group A Subgroup Testing

DC Characteristics

Parameters	Subgroups
V <sub>OH</sub>	1, 2, 3
V <sub>OL</sub>	1, 2, 3
V <sub>IH</sub>	1, 2, 3
V <sub>IL Max.</sub>	1, 2, 3
I <sub>Ix</sub>	1, 2, 3
I <sub>oz</sub>	1, 2, 3
I <sub>os</sub>	1, 2, 3
I <sub>CC</sub>	1, 2, 3
I <sub>SB1</sub>	1, 2, 3
I <sub>SB1</sub>	1, 2, 3

Switching Characteristics

Parameters	Subgroups
<b>READ CYCLE</b>	
t <sub>RC</sub>	7, 8, 9, 10, 11
t <sub>AA</sub>	7, 8, 9, 10, 11
t <sub>OHA</sub>	7, 8, 9, 10, 11
t <sub>ACE</sub>	7, 8, 9, 10, 11
t <sub>DOE</sub> <sup>(16)</sup>	7, 8, 9, 10, 11
<b>WRITE CYCLE</b>	
t <sub>WC</sub>	7, 8, 9, 10, 11
t <sub>SCE</sub>	7, 8, 9, 10, 11
t <sub>AW</sub>	7, 8, 9, 10, 11
t <sub>HA</sub>	7, 8, 9, 10, 11
t <sub>SA</sub>	7, 8, 9, 10, 11
t <sub>PWE</sub>	7, 8, 9, 10, 11
t <sub>SD</sub>	7, 8, 9, 10, 11
t <sub>HD</sub>	7, 8, 9, 10, 11

Note:  
16. 7C166A only.